SHEET 1 OF 1

INFORMATION DISCLOSURE ATTY, DOCKET NO. SERIAL NO. 10/756,830 055071-0329 CITATION IN AN APPLICATION **APPLICANT** Doug van den BROEKE, et al. FILING DATE **GROUP** (PTO-1449) January 14, 2004 2891 **U.S. PATENT DOCUMENTS** Publication Date Name of Patentee or Applicant of Cited Pages, Columns, Lines, Where **EXAMINER'S** Document Number INITIALS MM-DD-YYYY Relevant Passages or Relevant Document Number-Kind Codes (# known) Figures Appear 04-20-1999 US 5,895,741 Hasegawa et al. US 6,214,497 B1 04-10-2001 Stanton 2002/0152452 A1 10-17-2002 US Socha US 5,682,323 10-28-1997 Pasch et al. ÚS 6,303,253 B1 10-16-2001 Lu ับร 6,223,139 B1 04-24-2001 Wong et al. range IIS US IIS FOREIGN PATENT DOCUMENTS **EXAMINER'S** Foreign Patent Document **Publication Date** Name of Patentee or Pages, Columns, Lines Translation INITIALS Country Codes -Number 4 -Kind Applicant of Cited Document Where Relevant MM-DD-YYYY CITE Yes Codes (if known) Figures Appear NO 05-02-2002 ASMI Masktools RV EP 1 202 119 A1 rane **ADVANCED MICRO** WO 03/054626 A1 07-03-2003 NYME DEVICES, INC. OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.) Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, **EXAMINER'S** INITIALS journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where CITE published. NO. Christoph DOLAINSKY, et al., "Simulation based method for sidelobe suppression," Optical Microlithography XIII, Proceedings of SPIE, 2000, pp 1156-1162, Vol. 4000 Kyoji NAKAJO, et al., "Auxiliary pattern generation to cancel unexpected images at sidelobe overlap regions in attenuated phase-shift masks," Nicolas Bailey COBB, "Fast Optical and Process Proximity Correction Algorithms for Integrated Circuit Manufacturing," Ph.D. dissertation, Spring 1998, pp 35-72, University of California at Berkeley J. Fung CHEN, et al., "Practical I-Line OPC Contact Masks for Sub-0.3Micron Design Rule Application: Part 1—OPC Design Optimization," pp 181-201 J.A. TORRES, et al., "Contrast-Based Assist Feature Optimization," Optical Microlithography XV, 2002, pp 179-187, Proceedings of SPIE, Vol 4691, SPIE Olivier TOUBLAN, et al., "Fully Automatic Side Lobe Detection and Correction Technique for Attenuated Phase Shift Masks," Optical Microlithography XIV, 2001, pp 1541-1547, Proccedings of SPIE, Vol. 4346, SPIE Michael S. YEUNG, "Extension of the Hopkins theory of partially coherent imaging to include thin-film interference effects," Optical/Laser Microlithography VI, 1993, pp 452-463, SPIE, Vol. 1927 Douglas VAN DEN BROEKE, et al., "Near 0.3 k, Full Pitch Range Contact Hole Patterning Using Chromeless Phase Lithography (CPL)," Proceedings of the SPIE, September 9, 2003, pp 297-308, Vol. 5256, SPIE **DATE CONSIDERED EXAMINER**

15-06

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

INFORMATION DISCLOSURE CITATION IN AN					ATTY. DOCKET NO. 055071-0329	SERIAL NO. 10/756,830				
APPLICATION PE 40.					•					
					APPLICANT					
(PTO-1449) (FEB 21 2006 E					Doug van den BROEKE, et al.					
(PTO-1449) \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \					FILING DATE GROUP					
(F10-1449)					January 14, 2004 2891					
U.S. PATENT DOCUMENTS										
EXAMINER'S	CITE	Do	ocument Number	Publication Date	Name of Patentee or Applic		Pages, Columns, Lines, Where			
INITIALS NO.		Number-Kind Code2 (# known)		MM-OD-YYYY	Document		Relev	Relevant Passages or Relevant Figures Appear		
4:		US 5,229,230		07/20/1993	Kamon		_			
ame		US	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,							
11911		US 5,895,741 US 6,413,684 B1		04/20/1999	Hasegawa et al. Stanton					
04110			US 0,413,004 B1 07/02/2002		Stanton			_		
· · · · · · · · · · · · · · · · · · ·		US								
		US								
		US								
		บร								
		US								
		US								
		US								
		US								
FOREIGN PATENT DOCUMENTS										
EXAMINER'S Foreign Patent Document Publication Date Name of Patentee or Pages, Columns, Lines									anslation	
INITIALS	CITE NO.	Country	y Codes -Number 4 -Kind Codes (if known)	MM-DD-YYYY	Applicant of Cited Document	Where Relevant Figures Appear		Yes No		
CME		WO 02/03140 A1		01/10/2002	NUMERICAL TECHNOLOGIES, INC.			Х		
CME		EP 1 237 046 A2		09/04/2002	ASML MASKTOOLS B.V.			Х		
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)										
EXAMINER'S INITIALS CITE NO. Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.										
EXAMINER DATE CONSIDERED										
C. Jauchal 5-15-06										
*FXAMINER: Initial if reference considered whether or not citation is in conformance with MDED and Drow line through eligibles if not in exercises and not exercise.										

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.